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Appendix

List of Publications

1. Pankaow, N., Panyakeow, S., and Ratanathummaphan, S. Nanometer-scale $In_{0.5}Ga_{0.5}As$ ring-like structure grown by droplet epitaxy. Advanced Materials Research 31 (2008): 123-125.

2. Pankaow, N., Panyakeow, S., and Ratanathummaphan, S. Fabrication of In0.5Ga0.5As ring-and-hole structure by droplet molecular beam epitaxy. Journal of Crystal Growth 311 (2009): 1832-1835.

3. Pankaow, N., Panyakeow, S., and Ratanathummaphan, S. InGaAs RING-SHAPED NANOSTRUCTURES GROWN BY DROPLET EPITAXY. Compound Semiconductor Photonics: Materials, Devices and Integration. (2010): 152-154.

4. Pankaow, N., Thainoi, S., Panyakeow, S., and Ratanathummaphan, S. Surface morphology and photoluminescence of InGaAs quantum rings grown by droplet epitaxy with varying In0.5Ga0.5 droplet amount. Journal of Crystal Growth (2011) (accepted, in press).

5. Pankaow, N., Panyakeow, S., and Ratanathummaphan, S. $In_xGa_{1-x}As/GaAs$ Quantum Rings Grown by Droplet Epitaxy. AIP Proceedings of the International Conference on Physics of Semiconductor (ICPS2010) (2011) (accepted, in press).

List of Presentations

1. InGaAs/GaAs ring-like nanostructures grown by droplet using molecular beam epitaxy, Naraporn Pankaow, Somsak Panyakeow and Somchai Ratanathummaphan, 19th International Conference on Indium Phosphide and Related Materials (IPRM'07), Kunibiki Messe, Matsue, Japan, 14^{th}-18^{th} May, 2007.

2. Nanometer-scale $In_{0.5}Ga_{0.5}As$ ring-like structure grown by droplet epitaxy, Naraporn Pankaow, Somsak Panyakeow and Somchai Ratanathummaphan, 4^{th} International Conference on Materials for Advanced Technologies (ICMAT 2007), Singapore International Convention & Exhibition Centre, Singapore, 1^{st}-6^{th} July,2007.

3. Fabrication of In0.5Ga0.5As ring-and-hole structure by droplet molecular beam epitaxy, N. Pankaow, S. Panyakeow and S. Ratanathummaphan, 15^{th} International Conference on Molecular Beam Epitaxy (MBE 2008), University of British Columbia, Vancouver, Canada, 3^{rd}-8^{th} August, 2008.

4. InGaAs RING-SHAPED NANOSTRUCTURES GROWN BY DROPLET EPITAXY, Naraporn Pankaow, Somsak Panyakeow, Somchai Ratanathammaphan, International Conference on Materials for Advanced Technologies (ICMAT 2009), Suntec Centre, Singapore, 28^{th} May – 3^{rd} June, 2009.

5. Surface morphology and photoluminescence of InGaAs quantum rings grown by droplet epitaxy with varying In0.5Ga0.5 droplet amount, Naraporn Pankaow, Supachok Thainoi, Somsak Panyakeow, Somchai Ratanathammaphan, 16^{th} International Conference on Molecular Beam Epitaxy (MBE 2010), Berlin, Germany, 22^{nd}-27^{th} August, 2010.

6. $In_xGa_{1-x}As$/GaAs Quantum Rings Grown by Droplet Epitaxy, Naraporn Pankaow, Somsak Panyakeow, Somchai Ratanathammaphan, International Conference on Physics of Semiconductor (ICPS2010), Coex, Seoul, Korea, 25^{th}-30^{th} July, 2010.

VITAE

Naraporn Pankaow was born in Bangkok, Thailand on October 15th, 1983. She graduated from Chulalongkorn University demonstration in March 2001. In June 2001, she entered Chulalongkorn University and received the Bachelor of Engineering in field of Electrical Engineering with GPAX 3.35 in April 2005.

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